





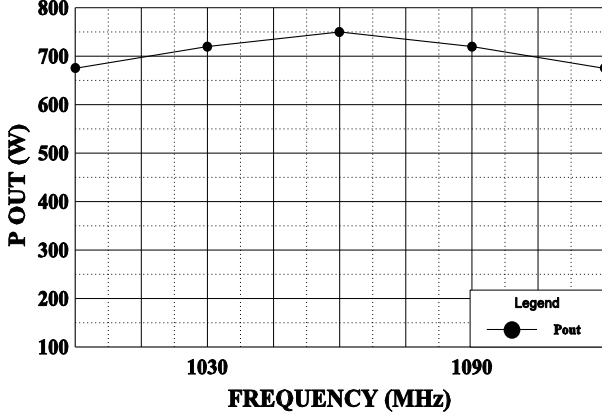
**GHZ TECHNOLOGY**  
RF · MICROWAVE SILICON POWER TRANSISTORS

# Typical Performance

## TPR 700

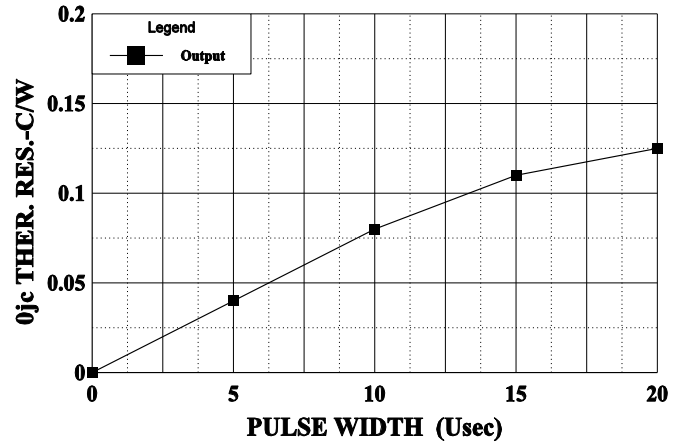
### POWER OUTPUT VS FREQUENCY

Vcc = 50 V, Pin = 150 W, PW = 10us, 1%



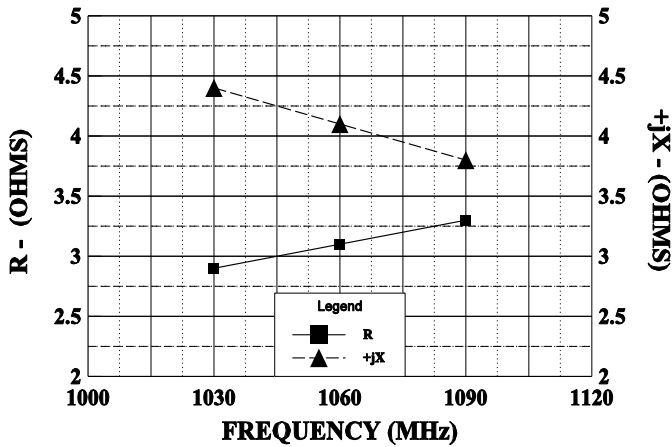
### THERMAL RESISTANCE VS PULSE WIDTH

Vcc = 50 V, Tf = 30 C



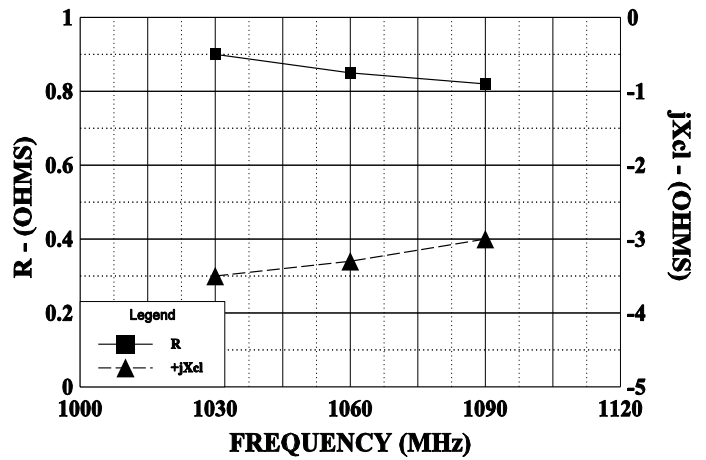
### SERIES INPUT IMPEDANCE VS FREQUENCY

Vcc = 50 V, Pin = 150 W, PW = 10us, 1%



### SERIES LOAD IMPEDANCE VS FREQUENCY

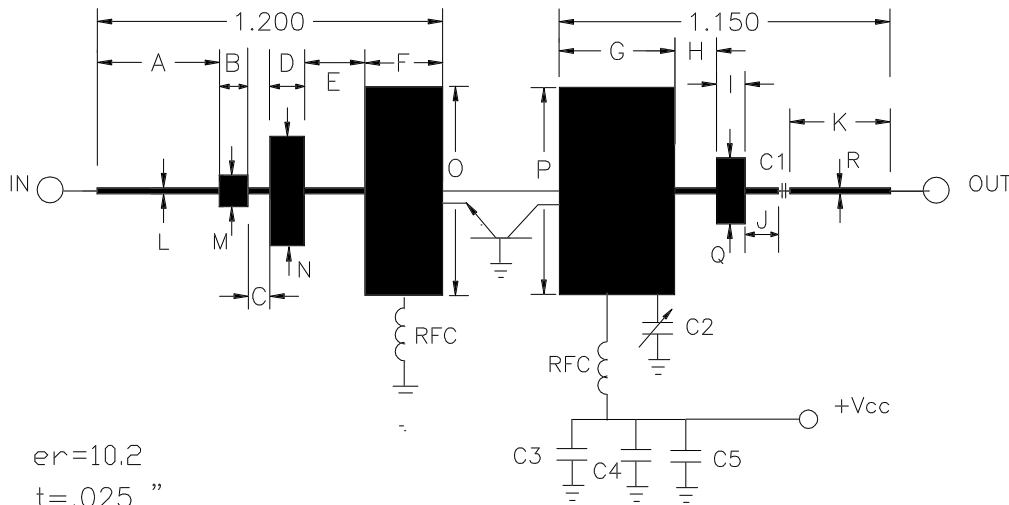
Vcc = 50 V, Po = 500 W, PW = 10us, 1%



REVISIONS

ZONE	REV	DESCRIPTION	DATE	APPROVED
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DIM	INCHES
A	.425
B	.100
C	.075
D	.120
E	.210
F	.270
G	.400
H	.145
I	.100
J	.115
K	.350
L	.021
M	.110
N	.380
O	.725
P	.720
Q	.230
R	.021



$\epsilon_r = 10.2$   
 $t = .025$  "  
 C1, C3 = 100 pf Chip  
 C2 = .3 - 3.5 pf  
 C4 = 1 uf  
 C5 = 220 uf

**GHZ TPR 700**  
 1030/1090 MHz

DATE: 5 OCT 95



**CHz TECHNOLOGY**

CAGE  
OPJR2

DWG NO.

**TPR 700**

REV  
**1**

SCALE

**1.5/1**

SHEET